Weida Hu

List of Publications by Citations

286 papers	13,869 citations	60 h-index	106 g-index
323 ext. papers	17,569 ext. citations	9.7 avg, IF	6.73 L-index

#	Paper	IF	Citations
286	Ultrasensitive and Broadband MoS₂ Photodetector Driven by Ferroelectrics. *Advanced Materials*, **2015**, 27, 6575-81	24	559
285	Progress, Challenges, and Opportunities for 2D Material Based Photodetectors. *Advanced Functional Materials*, **2019**, 29, 1803807	15.6	481
284	Photogating in Low Dimensional Photodetectors. *Advanced Science*, **2017**, 4, 1700323	13.6	372
283	Interlayer Transition and Infrared Photodetection in Atomically Thin Type-II MoTe₂/MoS₂ van der Waals Heterostructures. *ACS Nano*, **2016**, 10, 3852-8	16.7	314
282	Surface Plasmon-Enhanced Photodetection in Few Layer MoS2 Phototransistors with Au Nanostructure Arrays. *Small*, **2015**, 11, 2392-8	11	292
281	Room temperature high-detectivity mid-infrared photodetectors based on black arsenic phosphorus. *Science Advances*, **2017**, 3, e1700589	14.3	269
280	Van der Waals epitaxial growth and optoelectronics of large-scale WSe/SnS vertical bilayer p-n junctions. *Nature Communications*, **2017**, 8, 1906	17.4	258
279	Broadband Photovoltaic Detectors Based on an Atomically Thin Heterostructure. *Nano Letters*, **2016**, 16, 2254-9	11.5	248
278	ReS2-Based Field-Effect Transistors and Photodetectors. *Advanced Functional Materials*, **2015**, 25, 4076-4082	15.4	235
277	High Responsivity Phototransistors Based on Few-Layer ReS2 for Weak Signal Detection. *Advanced Functional Materials*, **2016**, 26, 1938-1944	15.6	217
276	Generalized colloidal synthesis of high-quality, two-dimensional cesium lead halide perovskite nanosheets and their applications in photodetectors. *Nanoscale*, **2016**, 8, 13589-96	7.7	215
275	Plasmonic Silicon Quantum Dots Enabled High-Sensitivity Ultrabroadband Photodetection of Graphene-Based Hybrid Phototransistors. *ACS Nano*, **2017**, 11, 9854-9862	16.7	209
274	Solution-processed graphene quantum dot deep-UV photodetectors. *ACS Nano*, **2015**, 9, 1561-70	16.7	206
273	Single InAs nanowire room-temperature near-infrared photodetectors. *ACS Nano*, **2014**, 8, 3628-35	16.7	202
272	Tunable Ambipolar Polarization-Sensitive Photodetectors Based on High-Anisotropy ReSe2 Nanosheets. *ACS Nano*, **2016**, 10, 8067-77	16.7	200
271	Ultrafast and broadband photodetectors based on a perovskite/organic bulk heterojunction for large-dynamic-range imaging. *Light: Science and Applications*, **2020**, 9, 31	16.7	194
270	Highly polarization sensitive infrared photodetector based on black phosphorus-on-WSe 2 photogate vertical heterostructure. *Nano Energy*, **2017**, 37, 53-60	17.1	185

269	Tailored Engineering of an Unusual (C H NH) (CH NH) Pb Br Two-Dimensional Multilayered Perovskite Ferroelectric for a High-Performance Photodetector. *Angewandte Chemie - International Edition*, **2017**, 56, 12150-12154	16.4	182
268	Recent Progress on Localized Field Enhanced Two-dimensional Material Photodetectors from Ultraviolet-Visible to Infrared. *Small*, **2017**, 13, 1700894	11	181
267	Arrayed Van Der Waals Broadband Detectors for Dual-Band Detection. *Advanced Materials*, **2017**, 29, 1604439	24	161
266	A self-powered high-performance graphene/silicon ultraviolet photodetector with ultra-shallow junction: breaking the limit of silicon?. *Npj 2D Materials and Applications*, **2017**, 1,	8.8	144
265	Palladium Diselenide Long-Wavelength Infrared Photodetector with High Sensitivity and Stability. *ACS Nano*, **2019**, 13, 2511-2519	16.7	144
264	High-responsivity graphene/InAs nanowire heterojunction near-infrared photodetectors with distinct photocurrent on/off ratios. *Small*, **2015**, 11, 936-42	11	140
263	. *IEEE Transactions on Electron Devices*, **2012**, 59, 1393-1401	2.9	134
262	Anomalous and highly efficient InAs nanowire phototransistors based on majority carrier transport at room temperature. *Advanced Materials*, **2014**, 26, 8203-9	24	133
261	High-Performance Photovoltaic Detector Based on MoTe /MoS Van der Waals Heterostructure. *Small*, **2018**, 14, 1703293	11	132
260	High efficiency and fast van der Waals hetero-photodiodes with a unilateral depletion region. *Nature Communications*, **2019**, 10, 4663	17.4	127
259	Highly sensitive visible to infrared MoTe2 photodetectors enhanced by the photogating effect. *Nanotechnology*, **2016**, 27, 445201	3.4	126
258	Stable mid-infrared polarization imaging based on quasi-2D tellurium at room temperature. *Nature Communications*, **2020**, 11, 2308	17.4	120
257	Arrayed van der Waals Vertical Heterostructures Based on 2D GaSe Grown by Molecular Beam Epitaxy. *Nano Letters*, **2015**, 15, 3571-7	11.5	119
256	Solution-Processed 3D RGO-MoS /Pyramid Si Heterojunction for Ultrahigh Detectivity and Ultra-Broadband Photodetection. *Advanced Materials*, **2018**, 30, e1801729	24	117
255	Enhanced Photoresponsivity of a GaAs Nanowire Metal-Semiconductor-Metal Photodetector by Adjusting the Fermi Level. *ACS Applied Materials & Interfaces*, **2019**, 11, 33188-33193	9.5	115
254	Epitaxial Ultrathin Organic Crystals on Graphene for High-Efficiency Phototransistors. *Advanced Materials*, **2016**, 28, 5200-5	24	109
253	Inch-Size Single Crystal of a Lead-Free Organic–Inorganic Hybrid Perovskite for High-Performance Photodetector. *Advanced Functional Materials*, **2018**, 28, 1705467	15.6	108
252	High-performance graphene photodetector using interfacial gating. *Optica*, **2016**, 3, 1066	8.6	104

251	When Nanowires Meet Ultrahigh Ferroelectric Field-High-Performance Full-Depleted Nanowire Photodetectors. *Nano Letters*, **2016**, 16, 2548-55	11.5	103
250	High-Sensitivity Floating-Gate Phototransistors Based on WS2 and MoS2. *Advanced Functional Materials*, **2016**, 26, 6084-6090	15.6	103
249	Perpendicular Optical Reversal of the Linear Dichroism and Polarized Photodetection in 2D GeAs. *ACS Nano*, **2018**, 12, 12416-12423	16.7	100
248	Perovskite-Erbium Silicate Nanosheet Hybrid Waveguide Photodetectors at the Near-Infrared Telecommunication Band. *Advanced Materials*, **2017**, 29, 1604431	24	99
247	Observation of ballistic avalanche phenomena in nanoscale vertical InSe/BP heterostructures. *Nature Nanotechnology*, **2019**, 14, 217-222	28.7	99
246	Programmable transition metal dichalcogenide homojunctions controlled by nonvolatile ferroelectric domains. *Nature Electronics*, **2020**, 3, 43-50	28.4	98
245	Transparent, high-performance thin-film transistors with an InGaZnO/aligned-SnO2 -nanowire composite and their application in photodetectors. *Advanced Materials*, **2014**, 26, 7399-404	24	91
244	Visible Light-Assisted High-Performance Mid-Infrared Photodetectors Based on Single InAs Nanowire. *Nano Letters*, **2016**, 16, 6416-6424	11.5	90
243	Ultrafast Dynamic Pressure Sensors Based on Graphene Hybrid Structure. *ACS Applied Materials & Interfaces*, **2017**, 9, 24148-24154	9.5	89
242	Near-Infrared Plasmonic 2D Semimetals for Applications in Communication and Biology. *Advanced Functional Materials*, **2016**, 26, 1793-1802	15.6	88
241	High-Performance Ferroelectric Polymer Side-Gated CdS Nanowire Ultraviolet Photodetectors. *Advanced Functional Materials*, **2016**, 26, 7690-7696	15.6	87
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235	Diamond-Based All-Carbon Photodetectors for Solar-Blind Imaging. *Advanced Optical Materials*, **2018**, 6, 1800068	8.1	71
234	Analysis of temperature dependence of dark current mechanisms for long-wavelength HgCdTe photovoltaic infrared detectors. *Journal of Applied Physics*, **2009**, 105, 104502	2.5	70

233	Recent Progress on Two-Dimensional Materials. *Wuli Huaxue Xuebao/ Acta Physico - Chimica Sinica*, **2021**, 2108017-0	3.8	69
232	Toward Sensitive Room-Temperature Broadband Detection from Infrared to Terahertz with Antenna-Integrated Black Phosphorus Photoconductor. *Advanced Functional Materials*, **2017**, 27, 1604414	15.6	68
231	A novel plasmonic resonance sensor based on an infrared perfect absorber. *Journal Physics D: Applied Physics*, **2012**, 45, 205102	3	66
230	Ferroelectric Localized Field-Enhanced ZnO Nanosheet Ultraviolet Photodetector with High Sensitivity and Low Dark Current. *Small*, **2018**, 14, e1800492	11	65
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209	Visible to near-infrared photodetectors based on MoS2 vertical Schottky junctions. *Nanotechnology* , **2017**,	3.4	51
208	Amorphous Gallium Oxide-Based Gate-Tunable High-Performance Thin Film Phototransistor for Solar-Blind Imaging. *Advanced Electronic Materials*, **2019**, 5, 1900389	6.4	50
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168	All-in-one two-dimensional retinomorphic hardware device for motion detection and recognition. *Nature Nanotechnology*, **2021**,	28.7	33
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165	Wafer-scale arrayed p-n junctions based on few-layer epitaxial GaTe. *Nano Research*, **2015**, 8, 3332-3341	10	32
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160	Ultrabroadband Photodetectors up to 10.6 μm Based on 2D Fe O Nanosheets. *Advanced Materials*, **2020**, 32, e2002237	24	29
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